



Prof. Geun Young Yeom

Education

Ph. D in Materials Science and Engineering, University of Illinois at Urbana-Champaign, USA	Sep. 84 – May 89
M.S. in Metallurgical Engineering, Seoul National University – Seoul, Korea	Mar. 81 - Feb. 83
B.S. in Metallurgical Engineering, Hanyang University – Seoul, Korea	Mar. 77 - Feb. 81

Professional Background

Professor, School of Advanced Materials Science & Engineering Sungkyunkwan University– Suwon, Korea	Mar. 92 – Present
Visiting Scholar, University of California at Berkeley, USA	Aug. 1999–Feb. 2001, Aug. 2009 – July 2011
Sr. Process Engineer, Silicon Systems Inc. Tustin– CA, USA	May. 05 – Feb. 99
Process Engineer / Researcher, Tektronix Inc. Beverton OR, USA	Aug. 89 – May. 9

Publication

- “Chlorine-trapped CVD bilayer graphene for resistive pressure sensor with high detection limit and high sensitivity,” 2D Mater. 4, 025049 (2017)
- “Atomic Layer Etching Mechanism of MoS₂ for Nanodevices”, ACS Appl. Mater. Interfaces 9, 11967 (2017)
- “Atomic layer etching of graphene through controlled ion beam for graphene-based electronics”, Scientific Reports Vol. 7 (2017)
- “Recent Advances in Doping of Molybdenum Disulfide:Industrial Applications and Future Prospects”,Adv. Mater. 28 (2016)
- “Cyclic chlorine trap-doping for transparent, conductive, thermally stable and damage-free graphene”, Nanoscale, (2014)
- “Understanding time-resolved processes in atomic-layer etching of ultra-thin Al₂O₃ film using BCl₃ and Ar neutral beam”, Applied Physics Letters, 105 (2014)
- “Atomic layer etching of graphene for full graphene device fabrication”, Carbon, 50 (2012) 5)